

IN THE CLAIMS:

Amendments to the Claims:

Please amend the claims as shown below.

Listing of Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A semiconductor device, comprising a laterally diffused field effect transistor including, over a semiconductor substrate, an element-forming area and a scribing area surrounding the element-forming area, the transistor including:

(a) a semiconductor layer of a first conductive type formed in the element-forming area over the semiconductor substrate,

(b) a gate insulating film formed over the semiconductor layer,

(c) a gate electrode formed over the gate insulating film,

(d) a source comprised of a first semiconductor region of a second conductive type ~~being~~ which is different from the first conductive type,

(e) a drain comprised of a second semiconductor region of the second conductive type having a first impurity concentration, and a third semiconductor region of the second conductive type having a higher second impurity concentration than the first impurity concentration and being formed at a position farther from the gate electrode than the second semiconductor region,

(f) a ~~forth~~ fourth semiconductor region of the first conductive type where a

channel region is formed,

(g) an electrode electrically connected to the source and formed over the rear surface of the semiconductor substrate, and

(h) a source electrode pad, for evaluation, formed in the element-forming area over the front surface of the semiconductor substrate and being electrically connected to the semiconductor substrate.

2. (original) The semiconductor device according to claim 1, wherein the source electrode pad for evaluation is not formed in the scribing area.

3. (original) The semiconductor device according to claim 1, wherein the source electrode pad for evaluation and the semiconductor substrate are connected to each other through a fifth semiconductor region of the first conductive type formed in the semiconductor layer.

4. (currently amended) The semiconductor device according to claim 1, wherein a passivation film is formed over the semiconductor substrate and the thickness from the rear surface of the semiconductor substrate to the front surface of the passivation film covering the source electrode pad ~~for evaluation~~ is 200 μm or less.

5. (currently amended) The semiconductor device according to claim 1, further comprising a drain electrode pad formed over the front surface of the

semiconductor substrate and being electrically connected to the third semiconductor region, and a gate electrode pad electrically connected to the gate electrode.

6. (currently amended) A semiconductor device, comprising a laterally diffused field effect transistor which includes:

(a) a semiconductor layer of a first conductive type formed over a semiconductor substrate;

(b) a gate insulating film formed over the semiconductor layer;

(c) a gate electrode formed over the gate insulating film;

(d) a source comprised of a first semiconductor region of a second conductive type being which is different from the first conductive type;

(e) a drain comprised of a second semiconductor region of the second conductive type having a first impurity concentration, and a third semiconductor region of the second conductive type having a higher second impurity concentration than the first impurity concentration and being formed at a position farther from the gate electrode than the second semiconductor region;

(f) a ~~forth~~ fourth semiconductor region of the first conductive type where a channel region is formed;

(g) a sixth semiconductor region of the first conductive type formed in the semiconductor layer and being a region for connecting electrically the first semiconductor region and the semiconductor substrate to each other; and

(h) a trench formed between the first semiconductor region and the sixth semiconductor region so as to extend from the front surface of the semiconductor

layer toward the semiconductor substrate.

7. (original) The semiconductor device according to claim 6, further comprising a source electrode pad for evaluation formed over the front surface of the semiconductor substrate and electrically connected to the semiconductor substrate.

8. (currently amended) The semiconductor device according to claim 6, further comprising a drain electrode pad formed over the front surface of the semiconductor substrate and being electrically connected to the third semiconductor region, and a gate electrode pad electrically connected to the gate electrode.

9. (original) The semiconductor device according to claim 6, wherein the depth of the trench is 2 μm or more.

10. (original) The semiconductor device according to claim 6, wherein an insulating film is embedded in the trench.

11. (original) The semiconductor device according to claim 6, wherein an electrically conductive film is embedded in the trench.

12. (original) The semiconductor device according to claim 6, wherein the trench is formed around the sixth semiconductor region.

13. (currently amended) The semiconductor device according to claim 6, wherein the trench restrains the sixth semiconductor region from spreading to the channel region.

Claims 14-20 (canceled)